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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/989,250	11/20/2001	Robertus Mominicus Joseph Verhaar	NL 000627	9630
24737	7590 04/24/2003			
PHILIPS ELECTRONICS NORTH AMERICAN CORP			EXAMINER	
	580 WHITE PLAINS RD TARRYTOWN, NY 10591		LUU, CHUONG A	
			ART UNIT	PAPER NUMBER
			2825	
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Please find below and/or attached an Office communication concerning this application or proceeding.

•	•	Application No.	Applicant(s)			
Office Action Summary		09/989,250	VERHAAR ET AL.			
		Examiner	Art Unit			
		Chuong A Luu	2825			
Period fo	The MAILING DATE of this communication app	ears on the cover sheet with the c	orrespondence addr ss			
A SHO THE N - Exter after - If the - If NO - Failur - Any r	ORTENED STATUTORY PERIOD FOR REPLY MAILING DATE OF THIS COMMUNICATION. Issions of time may be available under the provisions of 37 CFR 1.13 SIX (6) MONTHS from the mailing date of this communication. period for reply specified above is less than thirty (30) days, a reply period for reply is specified above, the maximum statutory period we to reply within the set or extended period for reply will, by statute, eply received by the Office later than three months after the mailing dipatent term adjustment. See 37 CFR 1.704(b).	6(a). In no event, however, may a reply be tim within the statutory minimum of thirty (30) days ill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	ely filed s will be considered timely. the mailing date of this communication. O (35 U.S.C. § 133).			
1) <u> </u>	Responsive to communication(s) filed on 10 F	ehruani 2003				
2a)□		s action is non-final.				
3)□	<i>,</i> —		osecution as to the merits is			
closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213.						
Disposition of Claims						
<ul> <li>4)⊠ Claim(s) 1-6 is/are pending in the application.</li> <li>4a) Of the above claim(s) is/are withdrawn from consideration.</li> </ul>						
		in nom consideration.				
·	5)  Claim(s) is/are allowed. 6)⊠ Claim(s) <u>1-6</u> is/are rejected.					
	Claim(s) is/are objected to.					
·	8) Claim(s) are subject to restriction and/or election requirement.					
Application Papers						
9) The specification is objected to by the Examiner.						
10) The drawing(s) filed on is/are: a) □ accepted or b) □ objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
11) The proposed drawing correction filed on is: a) ☐ approved b) ☐ disapproved by the Examiner.						
If approved, corrected drawings are required in reply to this Office action.						
12) The oath or declaration is objected to by the Examiner.						
Priority under 35 U.S.C. §§ 119 and 120						
13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).						
a) All b) Some * c) None of:						
1. Certified copies of the priority documents have been received.						
2. Certified copies of the priority documents have been received in Application No						
<ul> <li>3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>* See the attached detailed Office action for a list of the certified copies not received.</li> </ul>						
14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).						
<ul> <li>a) ☐ The translation of the foreign language provisional application has been received.</li> <li>15)☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.</li> </ul>						
Attachment(s)						
2) Notice	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice of Informal P	(PTO-413) Paper No(s) atent Application (PTO-152)			

## **DETAILED ACTION**

Applicant's arguments with respect to claims 1-6 have been considered but are moot in view of the new ground(s) of rejection.

## Inventorship

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

#### PRIOR ART REJECTIONS

# **Statutory Basis**

#### Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

# Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

## The Rejections

Claims 1 and 6 are rejected under 35 U.S.C. 102(e) as being anticipated by Lin et al. (U.S. 6,225,162 B1).

Lin discloses a method of fabrication a stacked-gate flash memory cell with

- (1) a substrate having a patterned ONO insulating layer over a portion thereof, and characterized by the steps of forming an insulating layer comprising an Oxide-Nitride-Silicon layered structure on the substrate, applying a photoresist to the silicon surface as part of a patterning process and stripping the photoresist once a required patterning process has been completed subsequently re-oxidizing the silicon layer of the remaining Oxide-Nitride-Silicon structure so as to form an ONO insulating layer structure (see column 5, lines 10-65. Figures 2c and 2i);
- (6) wherein the silicon layer is re-oxidized into a thermal oxide (see column 5, lines 50-60).

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Claim 2 is rejected under 35 U.S.C. 103(a) as being unpatentable over Lin et al. (U.S. 6,225,162 B1) in view of Prinz et al. (U.S. 6,133,093)

Lin discloses everything above except for wherein the silicon layer comprises an amorphous silicon layer. However, Prinz discloses a method for forming an integrated circuit with (2) wherein the silicon layer comprises an amorphous silicon layer (see column 5, lines 16-34). It would have been obvious to one having ordinary skill in the art at the time of the invention was made to combine the above teachings to fabricate a semiconductor device to exceed its performance criteria.

Claims 3-5 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lin et al. (U.S. 6,225,162 B1) in view of Shrivastava et al. (U.S. 6,133,602)

Lin teaches the above outlined features except for wherein a non-volatile memory cell is applied as part of the semiconductor structure, which non-volatile memory cell employs the ONO insulating layer between a floating gate and control gate thereof. However, Shrivastava discloses a method of fabricating a semiconductor device with (3) wherein a non-volatile memory cell is applied as part of the semiconductor structure, which non-volatile memory cell employs the ONO insulating layer between a floating gate and control gate thereof (see column 3, lines 51-62); (4) wherein a non-volatile memory cell is applied with a control gate formed from a conductive layer which also serves to form part of a peripheral semiconductor structure (see column 3, lines 51-62); (5) wherein the subsequent oxidation of the silicon sublayer of the Oxide-Nitride-Silicon insulating layer takes place also to provide a high voltage oxide layer for a peripheral structure (see columns 5 and 5, lines 7-17 and lines

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21-40, respectively). It would have been obvious to one having ordinary skill in the art

at the time of the invention was made to combine the above teachings to fabricate a

semiconductor device to exceed its performance criteria.

Conclusion

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Chuong A Luu whose telephone number is (703)305-

0129. The examiner can normally be reached on M-F (7:30-4:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Matthew Smith can be reached on (703)308-1323. The fax phone numbers

for the organization where this application or proceeding is assigned are (703)308-7722

for regular communications and (703)308-7724 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or

proceeding should be directed to the receptionist whose telephone number is (703)308-

0956.

April 21, 2003

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